

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

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Leakage currents in 4H-SiC JBS diodes

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<https://link.springer.com/article/10.1134/S106378261203013X>

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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